

HEXFET® Power MOSFET

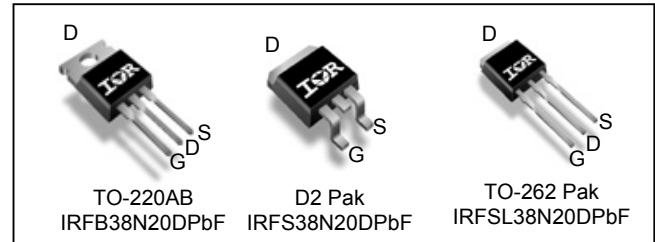
**Applications**

- High frequency DC-DC converters
- Plasma Display Panel

**Benefits**

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective  $C_{OSS}$  to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current
- Lead-Free

Key Parameters		
$V_{DS}$	<b>200</b>	<b>V</b>
$V_{DS(Avalanche) \text{ min.}}$	<b>260</b>	<b>V</b>
$R_{DS(on) \text{ max @ 10V}}$	<b>54</b>	<b>mΩ</b>
$T_J \text{ max}$	<b>175</b>	<b>°C</b>



<b>G</b>	<b>D</b>	<b>S</b>
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFB38N20DPbF	TO-220	Tube	50	IRFB38N20DPbF
IRFSL38N20DPbF	TO-262	Tube	50	IRFSL38N20DPbF
IRFS38N20DPbF	D2-Pak	Tube	50	IRFS38N20DPbF
		Tape and Reel Left	800	IRFS38N20DTRLpbF

**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$ ⑦	43*	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V$ ⑦	30*	
$I_{DM}$	Pulsed Drain Current ①	180	
$P_D @ T_A = 25^\circ\text{C}$	Maximum Power Dissipation ⑦	3.8	W
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation ⑦	300*	W
	Linear Derating Factor ⑦	2.0*	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	9.5	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	
	Mounting torque, 6-32 or M3 screw ⑥	10 lbf·in (1.1N·m)	

**Thermal Resistance**

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.47*	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface ⑥	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient ⑥	—	62	
$R_{\theta JA}$	Junction-to-Ambient ( PCB Mount, steady state) ⑦	—	40	

\*  $R_{\theta JC}$  (end of life) for D2Pak and TO-262 = 0.50°C/W. This is the maximum measured value after 1000 temperature cycles from -55 to 150°C and is accounted for by the physical wear out of the die attach medium.

Notes ① through ⑦ are on page 2.

**Static @ T<sub>J</sub> = 25°C (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	200	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	0.22	—	V/°C	Reference to 25°C, I <sub>D</sub> = 1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.054	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 26A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	3.0	—	5.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	25	μA	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V
		—	—	250		V <sub>DS</sub> = 160V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 30V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -30V

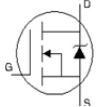
**Dynamic @ T<sub>J</sub> = 25°C (unless otherwise specified)**

g <sub>fs</sub>	Forward Trans conductance	17	—	—	S	V <sub>DS</sub> = 50V, I <sub>D</sub> = 26A
Q <sub>g</sub>	Total Gate Charge	—	60	91	nC	I <sub>D</sub> = 26A
Q <sub>gs</sub>	Gate-to-Source Charge	—	17	25		V <sub>DS</sub> = 100V
Q <sub>gd</sub>	Gate-to-Drain Charge	—	28	42		V <sub>GS</sub> = 10V ④
t <sub>d(on)</sub>	Turn-On Delay Time	—	16	—	ns	V <sub>DD</sub> = 100V
t <sub>r</sub>	Rise Time	—	95	—		I <sub>D</sub> = 26A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	29	—		R <sub>G</sub> = 2.5Ω
t <sub>f</sub>	Fall Time	—	47	—		V <sub>GS</sub> = 10V ④
C <sub>iss</sub>	Input Capacitance	—	2900	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	450	—		V <sub>DS</sub> = 25V
C <sub>riss</sub>	Reverse Transfer Capacitance	—	73	—		f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	3550	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 1.0V f = 1.0MHz
C <sub>oss</sub>	Output Capacitance	—	180	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 160V f = 1.0MHz
C <sub>oss eff.</sub>	Effective Output Capacitance	—	380	—		V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V to 160V ⑤

**Avalanche Characteristics**

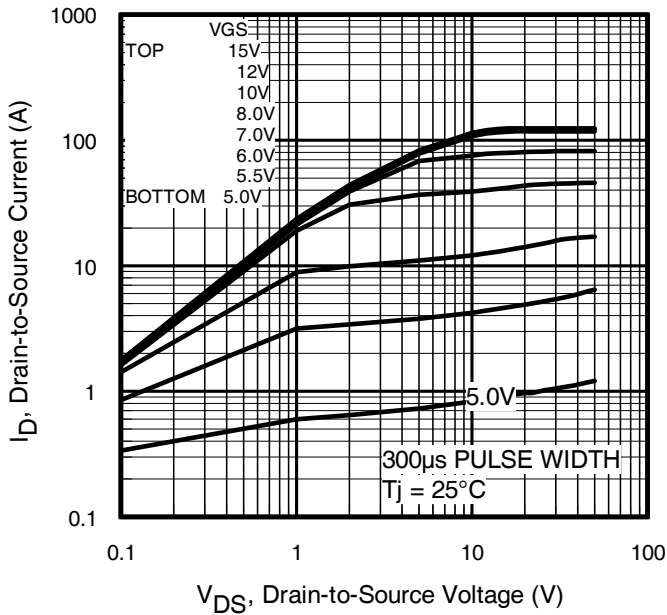
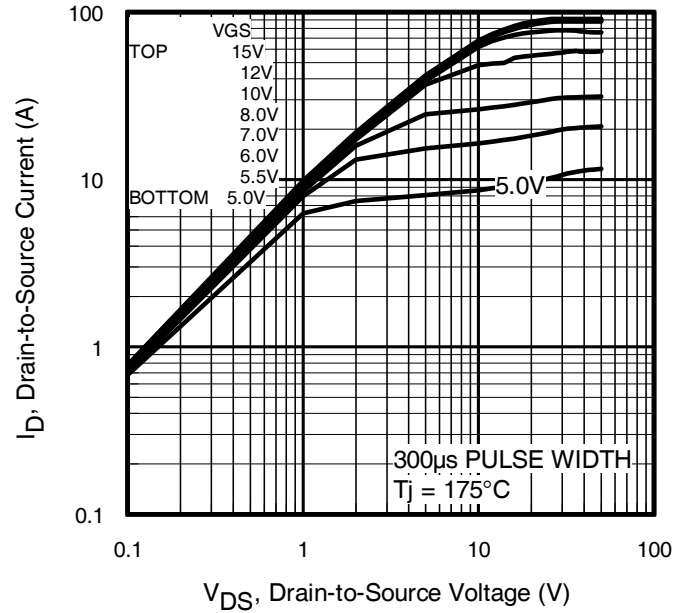
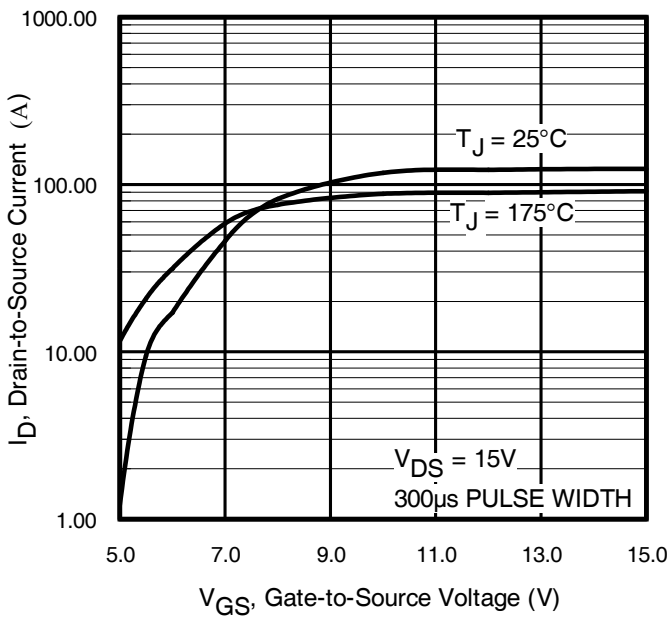
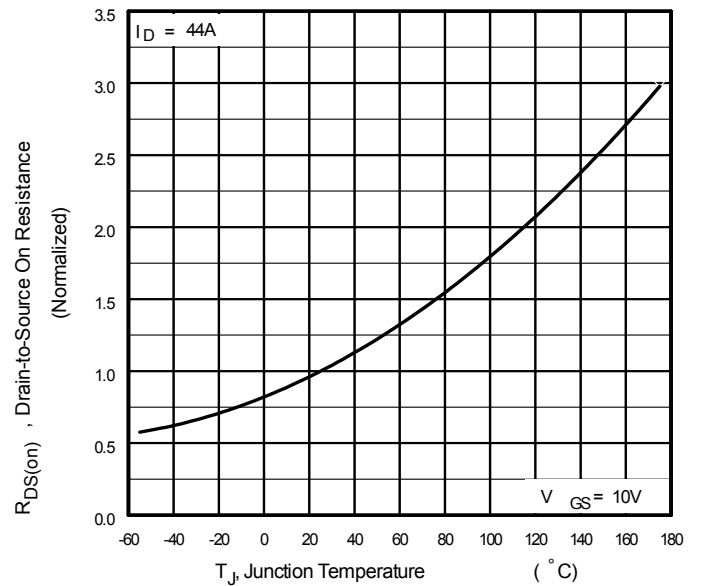
	Parameter	Min.	Typ.	Max.	Units
E <sub>AS</sub>	Single Pulse Avalanche Energy ②⑥	—	—	460	mJ
I <sub>AR</sub>	Avalanche Current ①	—	—	26	A
E <sub>AR</sub>	Repetitive Avalanche Energy ①	—	390	—	mJ
V <sub>DS (Avalanche)</sub>	Repetitive Avalanche Voltage ①	260	—	—	V

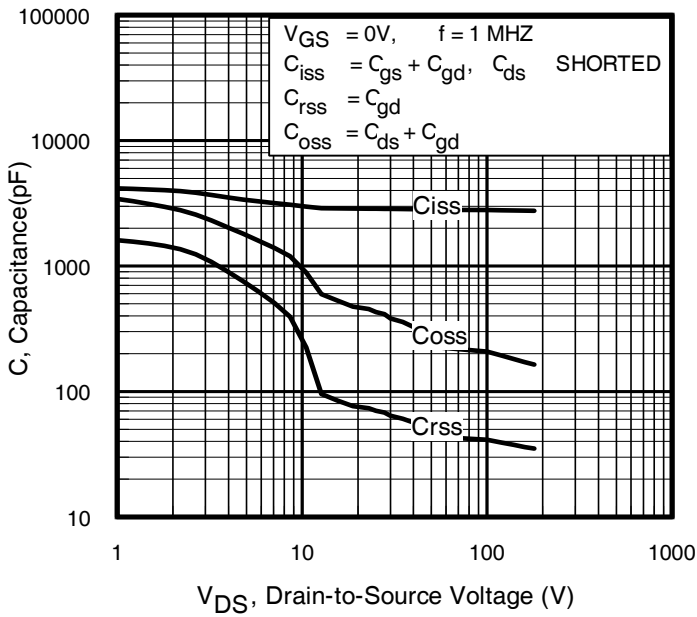
**Diode Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	44	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①⑥	—	—	180		
V <sub>SD</sub>	Diode Forward Voltage	—	—	1.5	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = 26A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	160	240	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = 26A
Q <sub>rr</sub>	Reverse Recovery Charge	—	1.3	2.0	μC	di/dt = 100A/μs ④
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

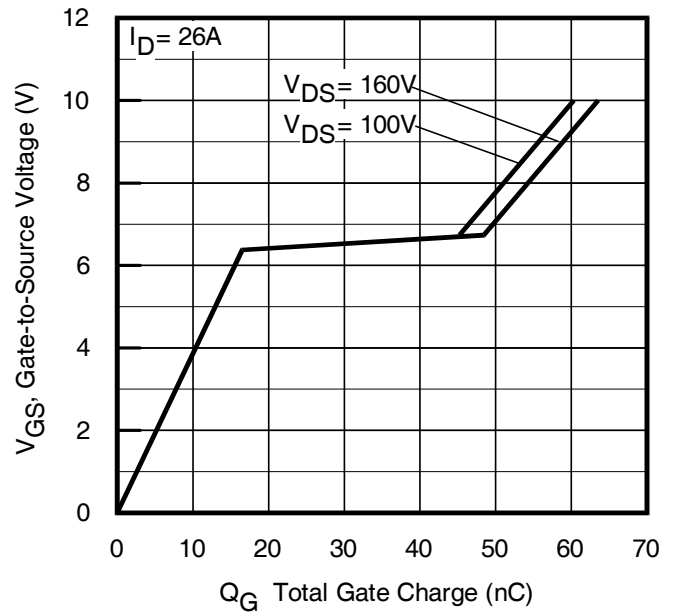
**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② starting T<sub>J</sub> = 25°C, L = 1.3mH, R<sub>G</sub> = 25Ω, I<sub>AS</sub> = 26A.
- ③ I<sub>SD</sub> ≤ 26A, di/dt ≤ 390A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 175°C.
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ C<sub>oss eff.</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>DSS</sub>.
- ⑥ This is only applied to TO-220AB package.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

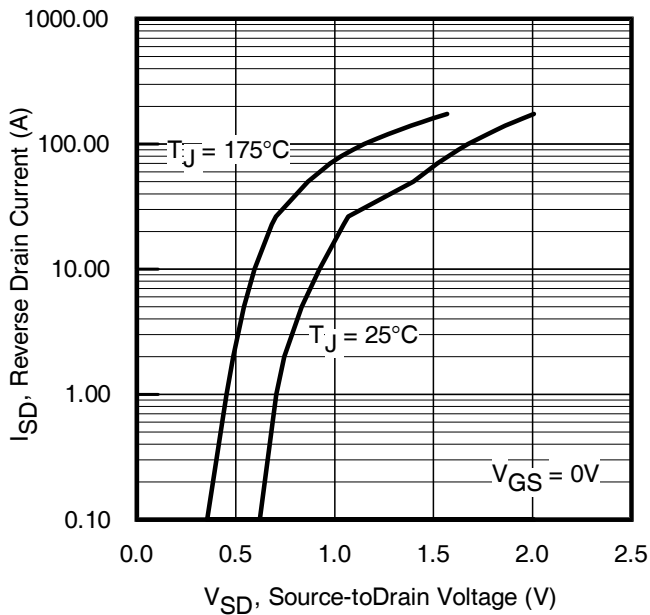

**Fig. 1** Typical Output Characteristics

**Fig. 2** Typical Output Characteristics

**Fig. 3** Typical Transfer Characteristics

**Fig. 4** Normalized On-Resistance vs. Temperature



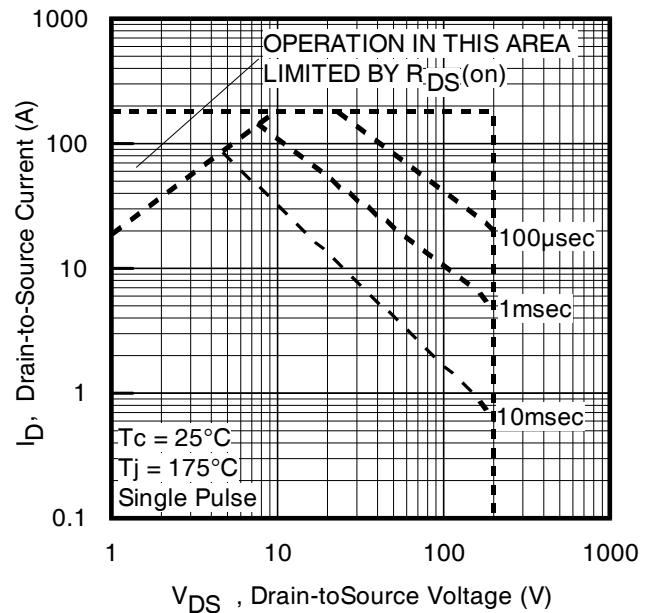
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



**Fig. 7** Typical Source-to-Drain Diode Forward Voltage



**Fig 8.** Maximum Safe Operating Area

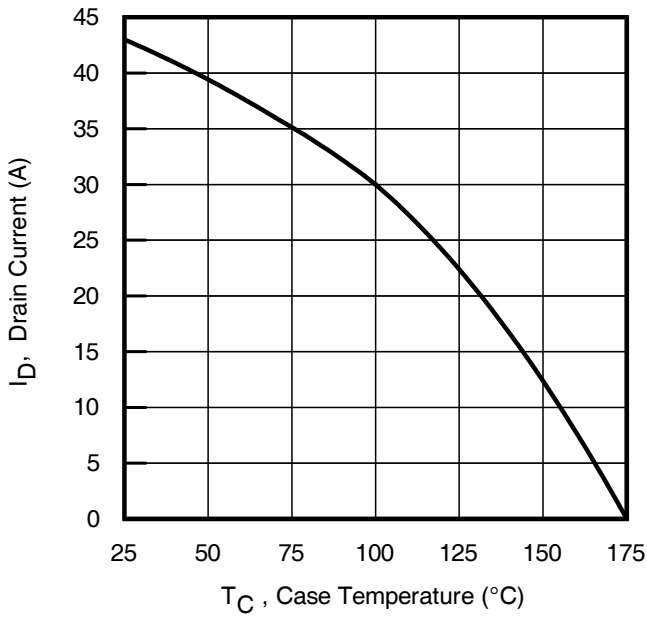


Fig 9. Maximum Drain Current vs. Case Temperature

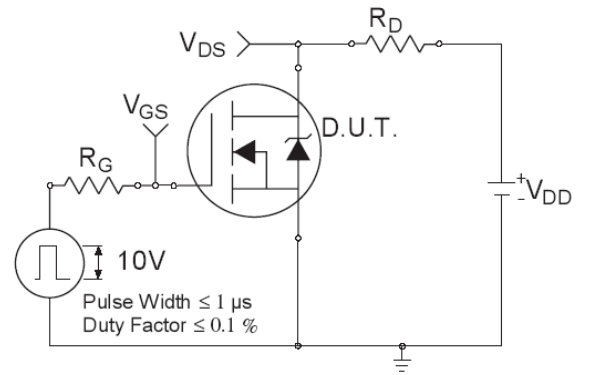


Fig 10a. Switching Time Test Circuit

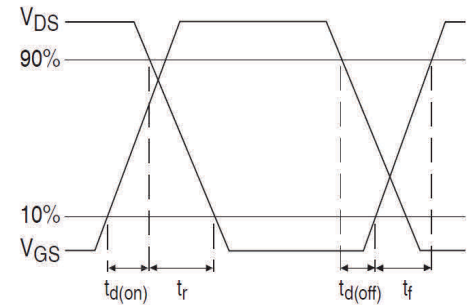


Fig 10b. Switching Time Waveforms

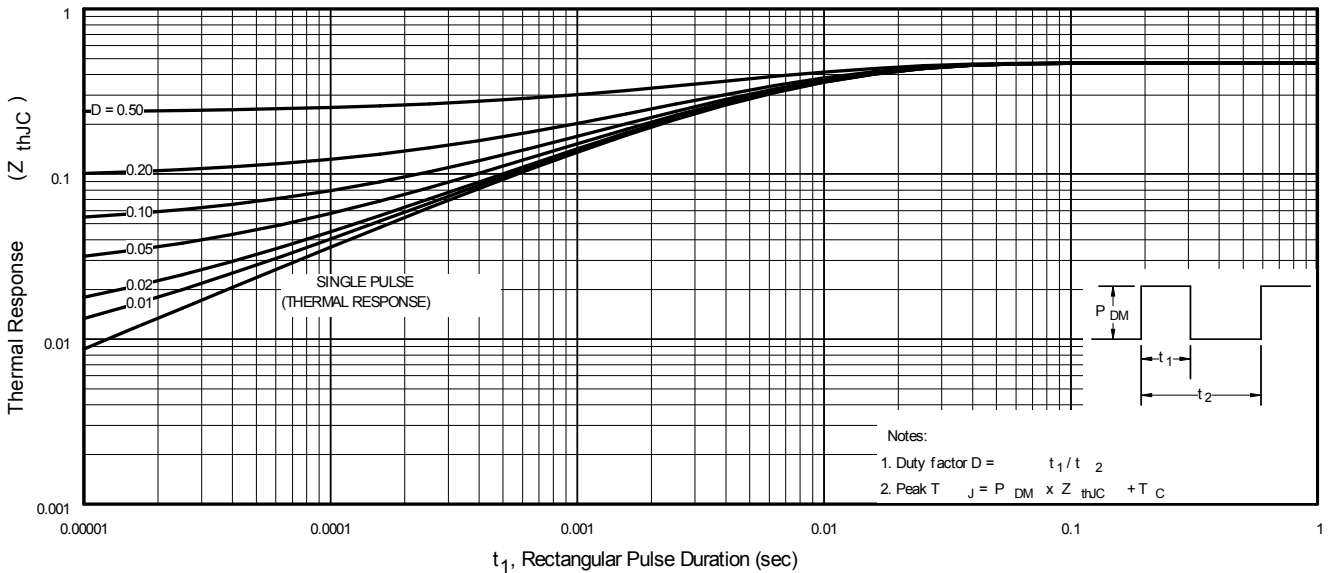
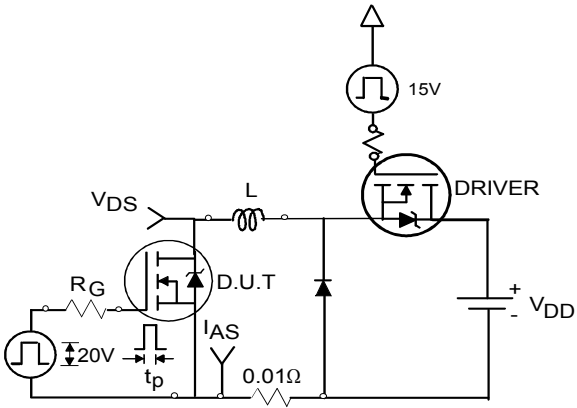
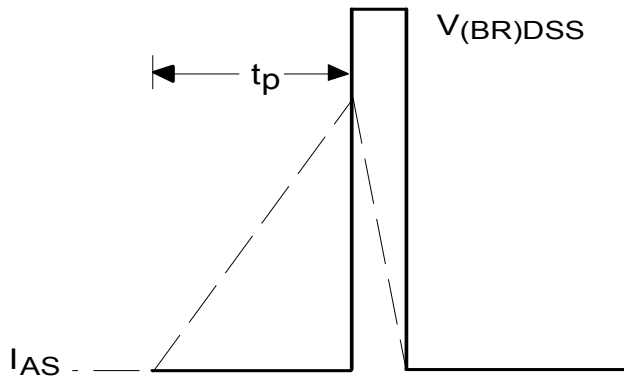
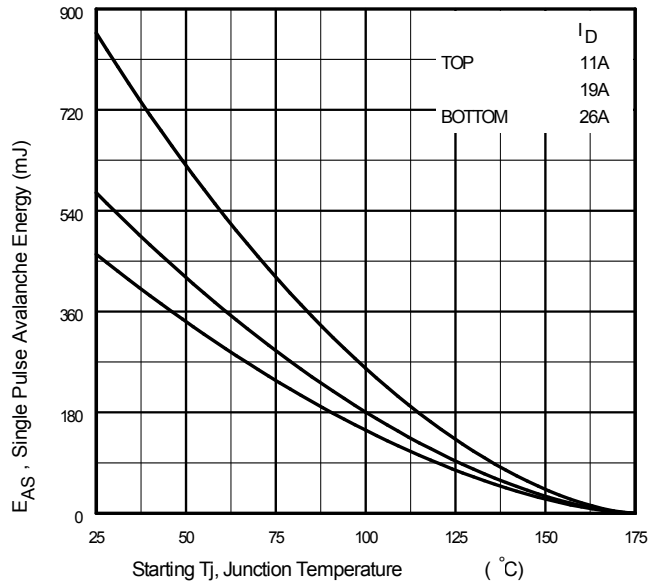
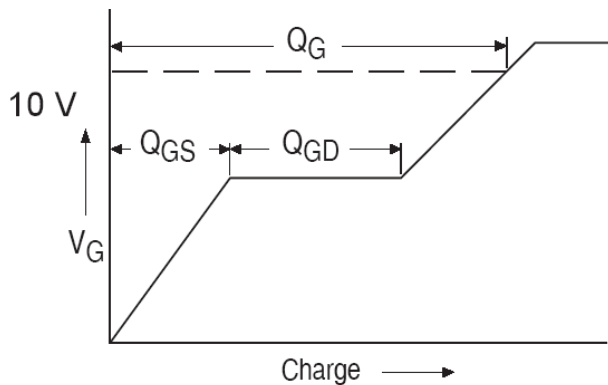
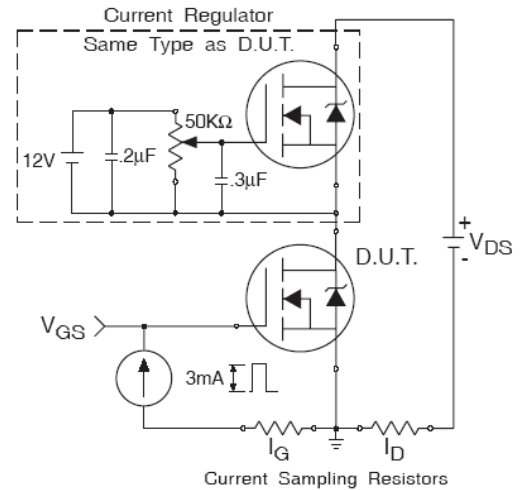
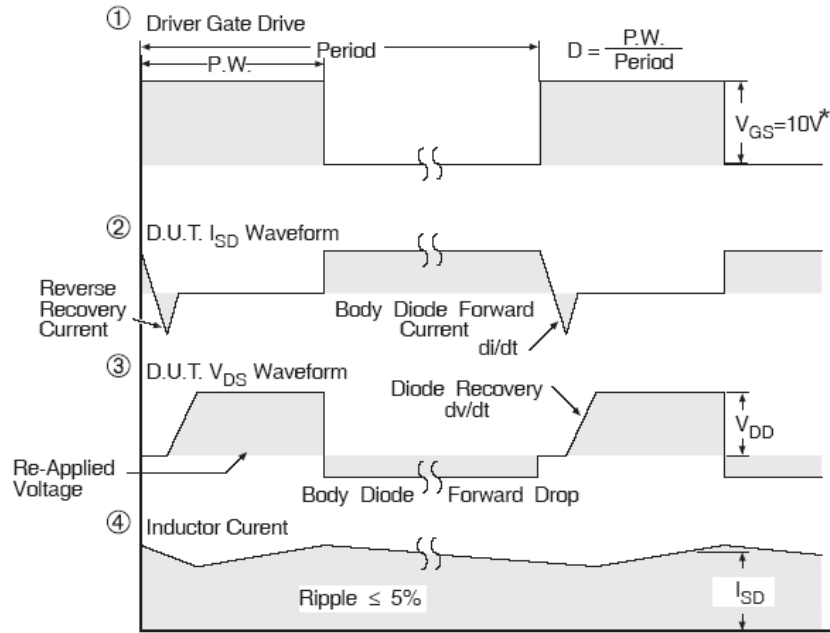
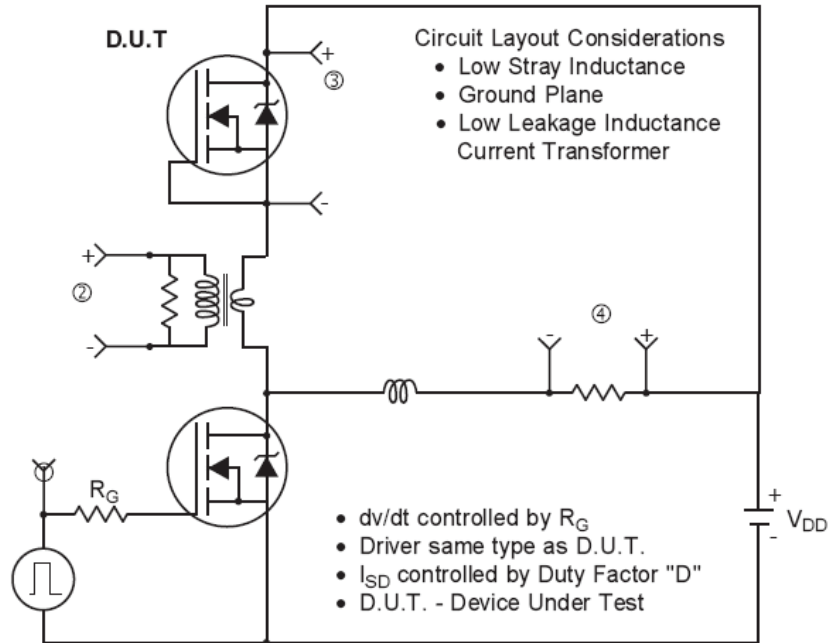


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

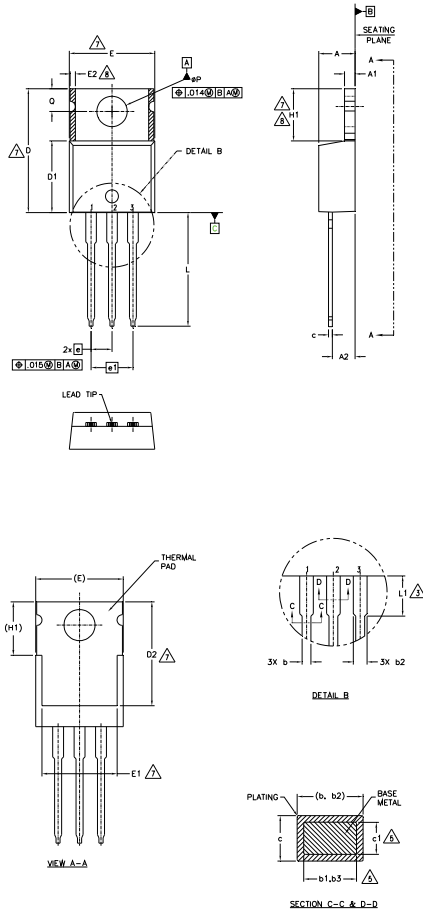

**Fig 12a. Unclamped Inductive Test Circuit**

**Fig 12b. Unclamped Inductive Waveforms**

**Fig 12c. Maximum Avalanche Energy vs. Drain Current**

**Fig 13a. Gate Charge Waveform**

**Fig 13b. Gate Charge Test Circuit**

### Peak Diode Recovery dv/dt Test Circuit



\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs

**TO-220AB Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994.
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
- 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN L1.
- 4.- DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 5.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
- 6.- CONTROLLING DIMENSION : INCHES.
- 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E,H1,D2 & E1
- 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
- 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	1.14	1.40	.045	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.68	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		100 BSC		
e1	5.08 BSC		200 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
øP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

**LEAD ASSIGNMENTS**
**HEMFEET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE

**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

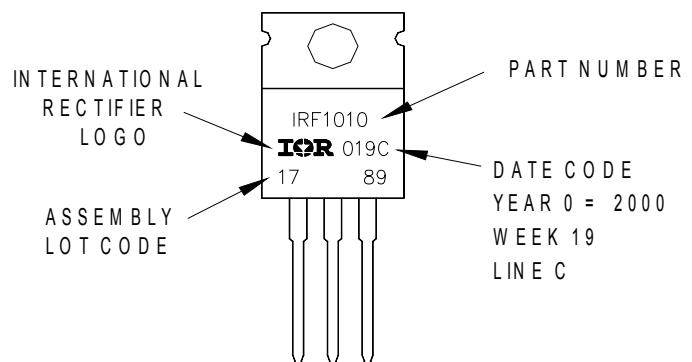
**DIODES**

- 1.- ANODE
- 2.- CATHODE
- 3.- ANODE

**TO-220AB Part Marking Information**

EXAMPLE: THIS IS AN IRF1010  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 2000  
 IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position  
 indicates "Lead - Free"

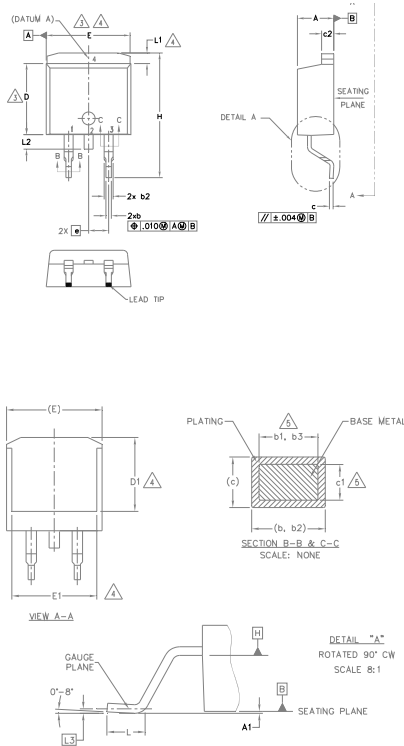


TO-220AB packages are not recommended for Surface Mount Application.

**Notes:**

1. For an Automotive Qualified version of this part please see <http://www.infineon.com/product-info/auto/>
2. For the most current drawing please refer to Infineon website at <http://www.infineon.com/package/>



**D2-Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))**

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [".005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	—	.270	—	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	—	.245	—	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	—	1.68	—	.066	4
L2	—	1.78	—	.070	
L3	0.25 BSC		.010 BSC		

**LEAD ASSIGNMENTS**
**DIODES**

- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
2. 4.- CATHODE
- 3.- ANODE

**HEXFET**

- 1.- GATE
2. 4.- DRAIN
- 3.- SOURCE

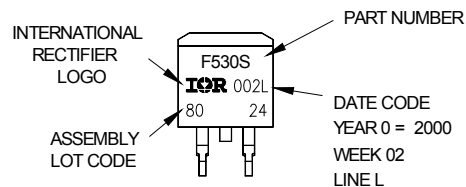
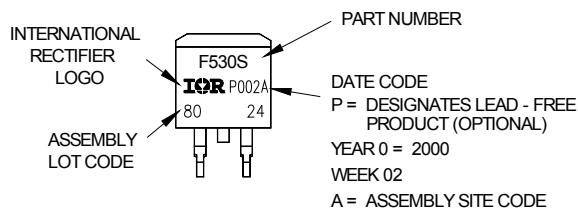
**IGBTs, CoPACK**

- 1.- GATE
2. 4.- COLLECTOR
- 3.- EMITTER

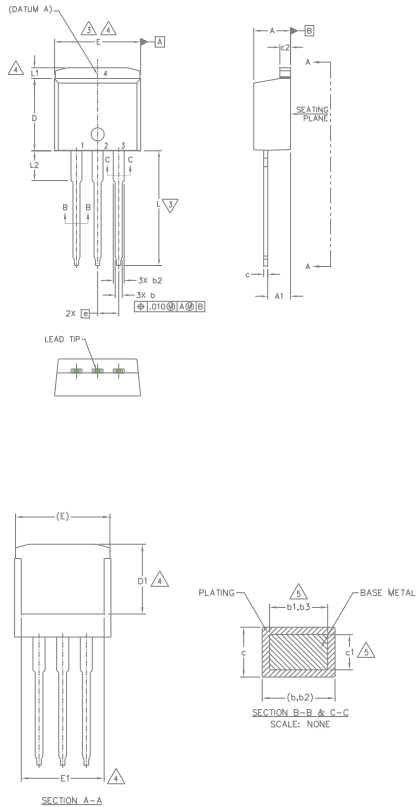
**D2-Pak (TO-263AB) Part Marking Information**

EXAMPLE: THIS IS AN IRF530S WITH  
LOT CODE 8024  
ASSEMBLED ON WW 02, 2000  
IN THE ASSEMBLY LINE "L"

Note: "P" in assembly line position  
indicates "Lead - Free"


**OR**

**Notes:**

1. For an Automotive Qualified version of this part please see <http://www.infineon.com/product-info/automotive>
2. For the most current drawing please refer to Infineon website at <http://www.infineon.com/package/>

**TO-262 Package Outline (Dimensions are shown in millimeters (inches))**


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
  2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
  3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
  4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
  5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
  6. CONTROLLING DIMENSION: INCH.
  7. OUTLINE CONFORM TO JEDEC TO-262 EXCEPT A1(max.), b(min.) AND D1(min.) WHERE DIMENSIONS DERIVED THE ACTUAL PACKAGE OUTLINE.

**LEAD ASSIGNMENTS**
**IGBTs, CoPACK**

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

**HEXFET**

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

**DIODES**

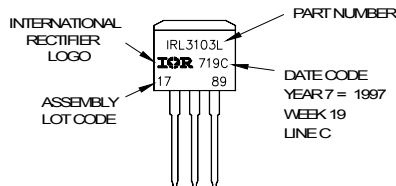
- 1.- ANODE (TWO DIE) / OPEN (ONE DIE)
- 2, 4.- CATHODE
- 3.- ANODE

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	3.02	.080	.119	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	-	.270	-	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	-	.245	-	4
e	2.54 BSC		.100 BSC		
L	13.46	14.10	.530	.555	
L1	-	1.65	-	.065	4
L2	3.56	3.71	.140	.146	

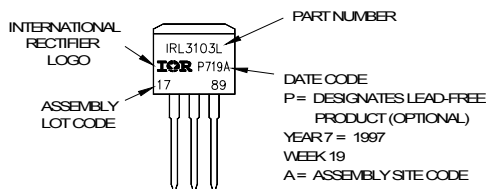
**TO-262 Part Marking Information**

EXAMPLE: THIS IS AN IRL3103L  
 LOT CODE 1789  
 ASSEMBLED ON WW19, 1997  
 IN THE ASSEMBLY LINE "C"

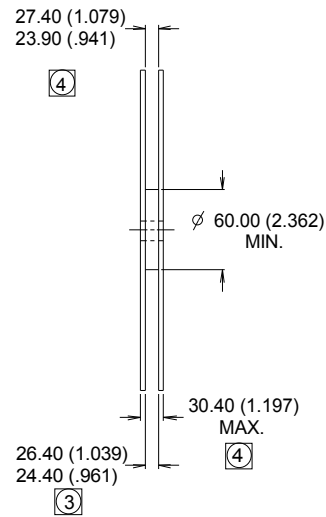
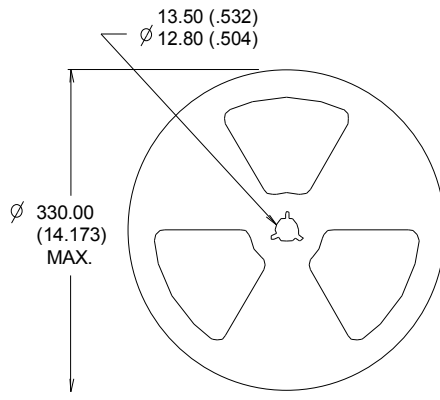
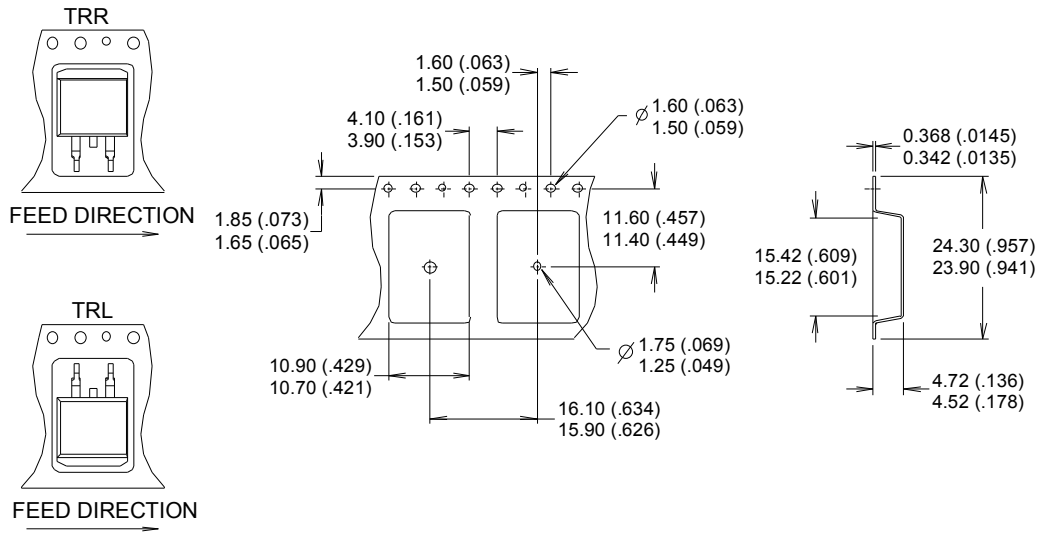
Note: "P" in assembly line position indicates "Lead - Free"



OR


**Notes:**

1. For an Automotive Qualified version of this part please see <http://www.infineon.com/product-info/auto/>
2. For the most current drawing please refer to Infineon website at <http://www.infineon.com/package/>

**D2-Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))**

**NOTES :**

1. CONFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

**Qualification Information†**

Qualification Level	Industrial (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	TO-220AB	N/A
	D2-Pak	MSL1 (per JEDEC J-STD-020D) ††
	TO-262	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at Infineon’s web site [www.infineon.com](http://www.infineon.com)

†† Applicable version of JEDEC standard at the time of product release.

**Revision History**

Date	Comments
5/31/2016	<ul style="list-style-type: none"> <li>Updated datasheet with corporate template.</li> <li>Added disclaimer on last page.</li> </ul>

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